

99. (New) The method for fabricating the semiconductor device as claimed in claim 98, wherein the sealing resin used in the resin sealing step has an amount which causes the resin layer to have a height approximately equal to that of the protruding electrodes.

100. (New) The method for fabricating the semiconductor device as claimed in claim 98, wherein the resin sealing step uses a sheet-shaped resin as the sealing resin.

101. (New) The method for fabricating the semiconductor device as claimed in claim 98, wherein the protruding electrode exposing step uses means for exposing the ends thereof from the resin layer, said means being at least one of a laser beam projection, eximer laser, etching, mechanical polishing, and blasting.

102. (New) The method for fabricating the semiconductor device as claimed in claim 98, wherein the sealing resin used in the resin sealing step comprises a plurality of sealing resins having different characteristics.

103. (New) The method for fabricating the semiconductor device as claimed in claim 98, wherein a second resin layer is formed so as to cover a back surface of the substrate after or at the same time as the first resin layer is formed, in the resin sealing step, on the surface of the substrate on which the protruding electrodes are arranged.

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104. (New) A method for fabricating semiconductor devices comprising:  
a resin sealing step of loading a substrate on which semiconductor elements having external connection electrodes formed on surfaces of the semiconductor elements onto a mold and supplying a resin to the surfaces so that a resin layer sealing the external connection electrodes and the substrate is formed; and  
a separating step of cutting the substrate together with the resin layer in positions in which the external connection electrodes are formed, so that the semiconductor elements are separated from each other.

105. (New) The method for fabricating the semiconductor devices as claimed in claim 104, wherein the external connection electrodes are commonly included by adjacent ones of the semiconductor elements before the separating step is executed.

106. (New) A method for fabricating a semiconductor device comprising:  
a resin sealing step of loading a wiring board having a flexible member on which a semiconductor element and leads are arranged onto a mold and supplying sealing resin to the semiconductor element so as to seal the semiconductor element; and  
a protruding electrode forming step of forming protruding electrodes so as to be electrically connected to the leads formed on the wiring board,  
the resin sealing step using a compression molding process.

107. (new) A method for fabricating the semiconductor as claims in claim 98, wherein the resin sealing step disposes a film between the substrate and the mold.

108. (New) A method for fabricating a semiconductor device, comprising the steps of: forming a groove in a predetermined region of a semiconductor wafer; sealing a surface of said semiconductor wafer including said groove and a sidewall surface of a protruding electrode formed on said semiconductor wafer; and dividing said semiconductor wafer on said groove into plural semiconductor devices.

109. (New) A method for fabricating a semiconductor device, comprising the steps of: forming two parallel grooves on a predetermined region of a semiconductor wafer; sealing a surface of said semiconductor wafer including said grooves and a sidewall surface of a protruding electrode formed on said semiconductor wafer; and dividing said semiconductor wafer at a position between said grooves into plural semiconductor devices.

110. (New) A method as claimed in claim 98, wherein said protruding electrode exposing step is conducted by pressing said seal resin layer.